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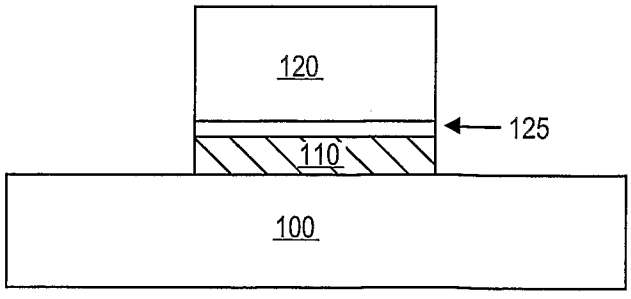
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(54) Title: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC



(57) Abstract: A method for making a semiconductor device is described. That method comprises forming a high-k gate dielectric layer (110) on a substrate (100), then forming a capping (115) layer on the high-k gate dielectric layer. After oxidizing the capping layer to form a capping dielectric oxide (125) on the high-k gate dielectric layer, a gate electrode (120) is formed on the capping dielectric oxide.

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